
2SC3380

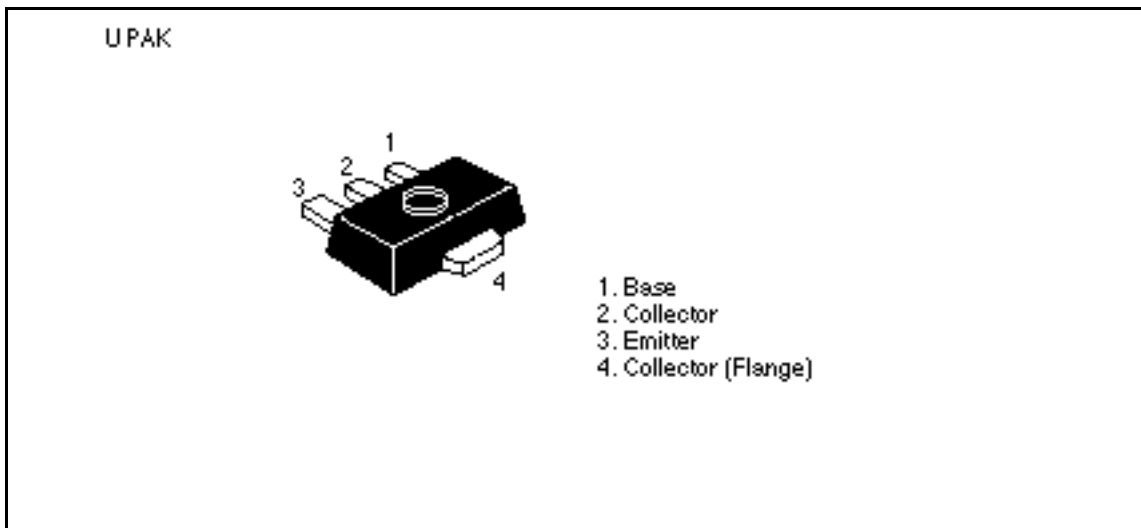
Silicon NPN Triple Diffused

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Application

- High frequency high voltage amplifier
- High voltage switch

Outline



Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	300	V
Collector to emitter voltage	V_{CEO}	300	V
Emitter to base voltage	V_{EBO}	5	V
Collector current	I_C	100	mA
Collector power dissipation	P_C^{*1}	1	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

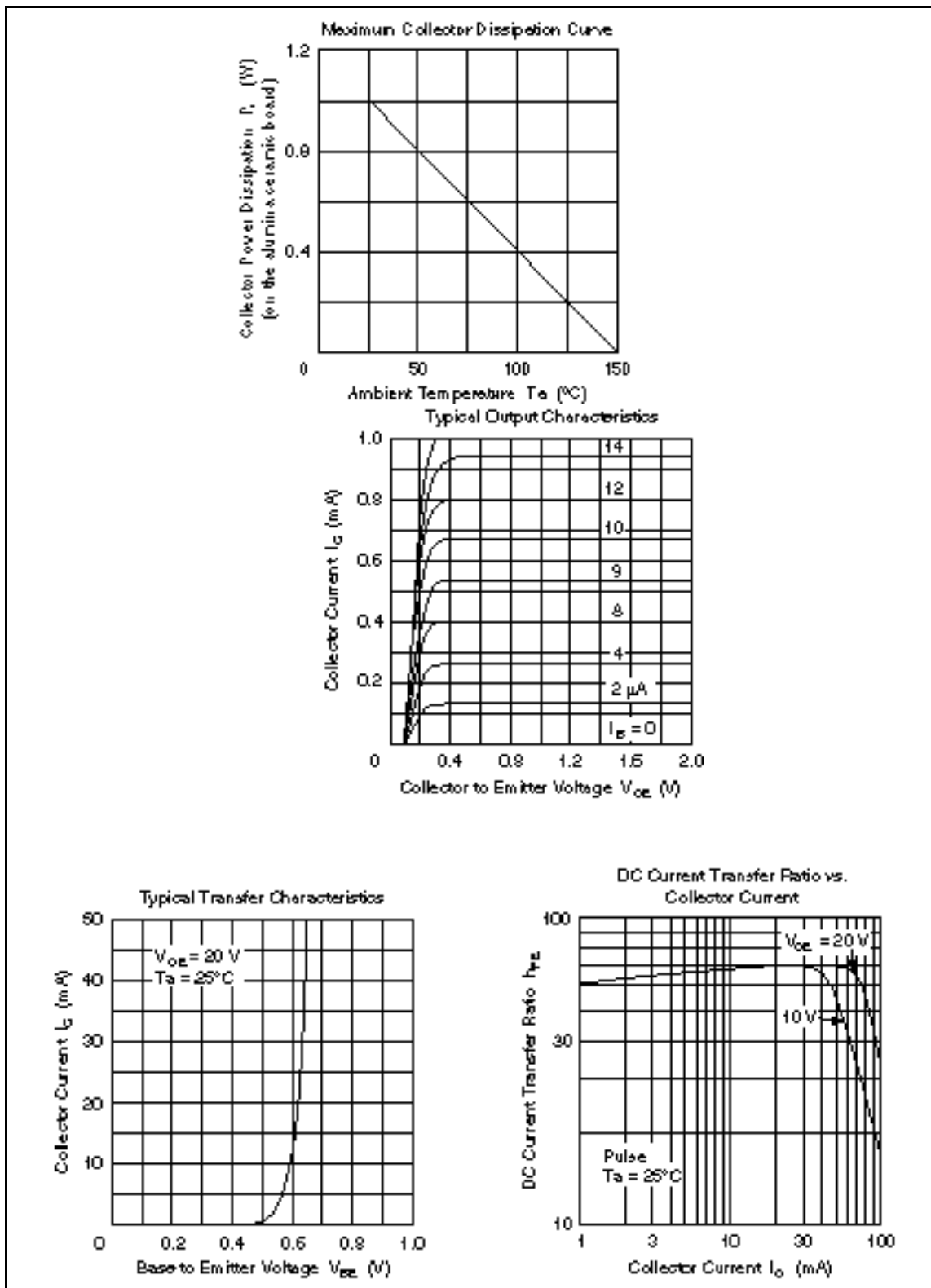
Note: 1. Value on the alumina ceramic board (12.5 × 20 × 0.7 mm)

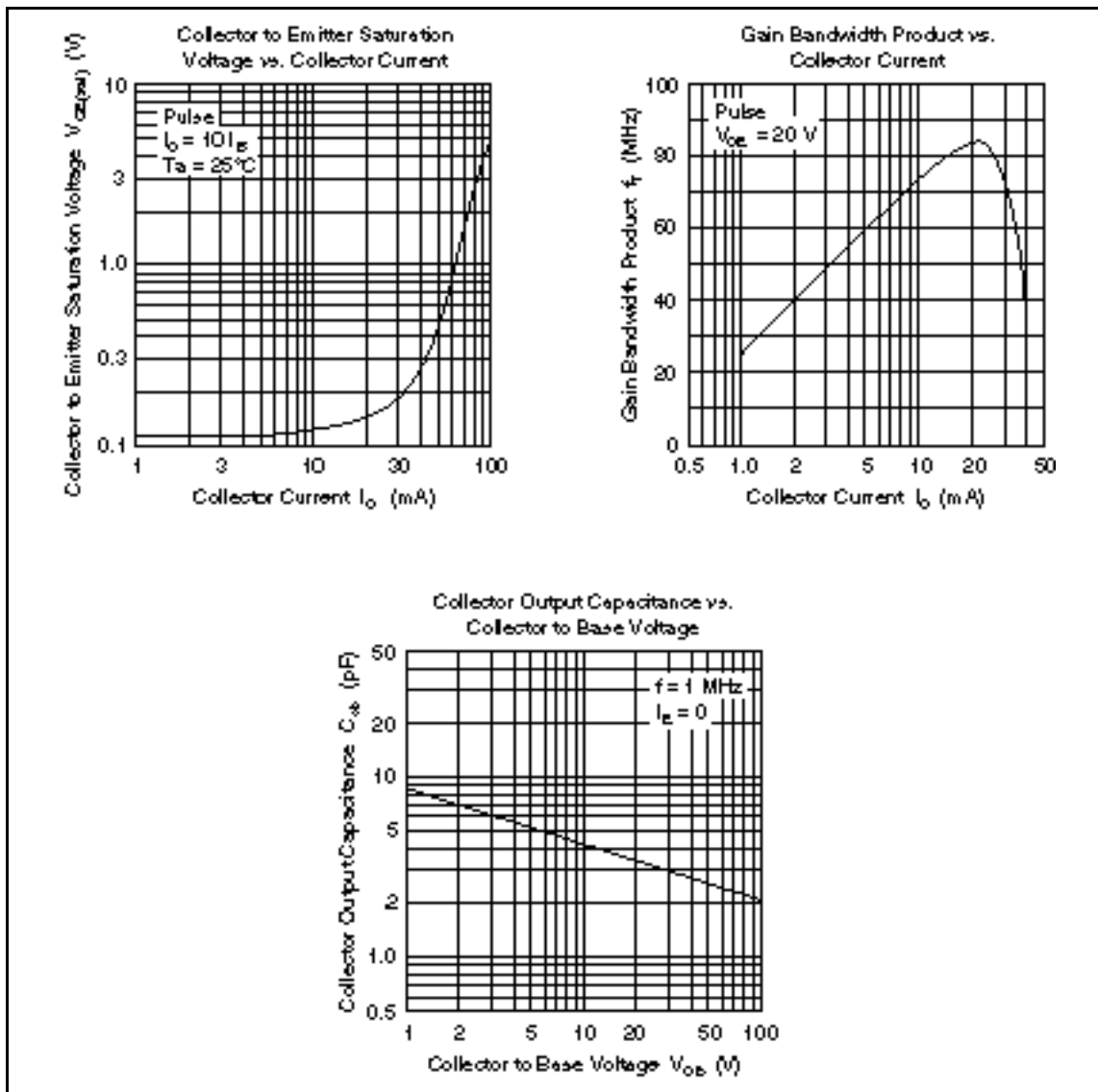
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Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	300	—	—	V	$I_C = 10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	300	—	—	V	$I_C = 1 \text{ mA}, R_{BE} =$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	—	—	V	$I_E = 10 \mu A, I_C = 0$
Collector cutoff current	I_{CEO}	—	—	1	μA	$V_{CE} = 250 \text{ V}, R_{BE} =$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	1.5	V	$I_C = 20 \text{ mA}, I_B = 2 \text{ mA}$
DC current transfer ratio	h_{FE}	30	—	200		$V_{CE} = 20 \text{ V}, I_C = 20 \text{ mA}$
Gain bandwidth product	f_T	—	80	—	MHz	$V_{CE} = 20 \text{ V}, I_C = 20 \text{ mA}$
Collector output capacitance	C_{ob}	—	—	4	pF	$V_{CB} = 20 \text{ V}, I_E = 0, f = 1 \text{ MHz}$

Note: Marking is "AS".





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